

2500-2700 MHz, 4 W Avg., 28 V WiMAX RF LDMOS Wideband Integrated Power Amplifiers, RF Amplifier HV7 2700MHz 4W TO272WB16

Manufacturers	<u>NXP Semiconductor</u>
Package/Case	TO-272
Product Type	RF Integrated Circuits
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for MW7IC2725NBR1 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

MW7IC2725NBR1 is a product part number for a GaN (Gallium Nitride) high-electron-mobility transistor (HEMT) manufactured by NXP Semiconductors.

Features

Frequency range: 2700-2900 MHz

Output power: 48.5 dBm (70 W) at 28 V

Efficiency: 58%

Gain: 21 dB

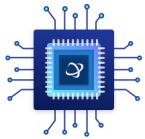


Related Products



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TO-270-16



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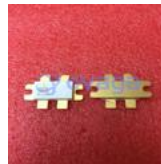
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